

<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application No.	10/678,766
<i>(Multiple sheets used when necessary)</i>		Filing Date	October 2, 2003
SHEET 1 OF 2		First Named Inventor	Tois et al.
		Art Unit	1792
		Examiner	Matthew J. Song
		Attorney Docket No.	SEPP21.001C1

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
	1	5,187,241	02-16-1993	Buchwalter et al.	
	2	5,496,597	03-05-1996	Soininen et al.	
	3	5,505,991	04-09-1996	Schmid et al.	
	4	5,603,750	02-18-1997	Sierakowski et al.	
	5	5,917,571	06-29-1999	Shimada	
	6	5,928,791	07-27-1999	Rosenmayer	
	7	6,174,809	01-16-2001	Kang et al.	
	8	6,492,528	12-10-2002	Matsuba et al.	
	9	6,613,383	09-02-2003	George et al.	
	10	6,818,517	11-16-2004	Maes	
	11	6,835,417	12-28-2004	Saenger et al.	
	12	6,858,546	02-22-2005	Niinisto et al.	
	13	7,045,170	05-16-2006	Hankins et al.	
	14	2006/0211259	09-21-2006	Maes et al.	

<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
	15	JP 03082769 A	04-1991	Tanaka, Naoto	
	16	JP 06080413 A	03-1994	Maruyama, Toshiro	
	17	JP 53148282 A	12-1978	Usuki et al.	

<b>NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>1</sup>
	18	ESAKI, L.; R. Tsu. "Superlattice and Negative Differential Conductivity in Semiconductors," <i>IBM J.Res. Develop.</i> , January 1970.			Abstract
	19	GASSER et al., "Quasi-monolayer deposition of silicon dioxide", <i>Thin Solid films</i> , 250 (1994) pg. 213-218.			Abstract
	20	LESKELA et al., "ALD precursor chemistry: Evolution and future challenges," <i>J. Phys. IV France</i> 9: 837-847 (1999).			

Examiner Signature	Date Considered
*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

T<sup>1</sup> - Place a check mark in this area when an English language Translation is attached.

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	21	MORISHITA et al, "New Substances for Atomic-Layer Deposition of Silicon Dioxide," <i>Journal of Non-Crystalline Solids</i> , 187 (1995) pg 66-69.	

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